

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE7190H uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

- $V_{DS} = 71V, I_D = 90A$   
 $R_{DS(ON)} < 6.8m\Omega @ V_{GS}=10V$  (Typ:5.9m $\Omega$ )
- Special process technology for high ESD capability
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

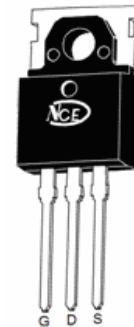
**100%  $\Delta V_d$ s TESTED!**



Schematic diagram



Marking and pin assignment



TO-220H-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE7190H	NCE7190H	TO-220-3L	-	-	-

### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	71	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	90	A
Drain Current-Continuous( $T_C=100^\circ C$ )	$I_D(100^\circ C)$	63	A
Pulsed Drain Current	$I_{DM}$	320	A
Maximum Power Dissipation	$P_D$	170	W
Derating factor		1.13	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	550	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta jc}$	0.88	$^{\circ}\text{C/W}$
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## Electrical Characteristics ( $T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	71	74	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=71V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$	-	5.9	6.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=40A$	-	50	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Gate resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, F=1.0\text{MHz}$	-	0.63	-	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	4871	-	PF
Output Capacitance	$C_{oss}$		-	630.6	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	410.3	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=30A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	36.1	-	nS
Turn-on Rise Time	$t_r$		-	54.3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	85.2	-	nS
Turn-Off Fall Time	$t_f$		-	37.3	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=48V, I_D=30A,$ $V_{GS}=10V$	-	85.7	-	nC
Gate-Source Charge	$Q_{gs}$		-	23.2	-	nC
Gate-Drain Charge	$Q_{gd}$		-	31.2	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=20A$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$	-	-	-	90	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = 40A$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	88.3	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	65.9	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=35V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

## Test Circuit

### 1) E<sub>AS</sub> test Circuit



### 2) Gate charge test Circuit



### 3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

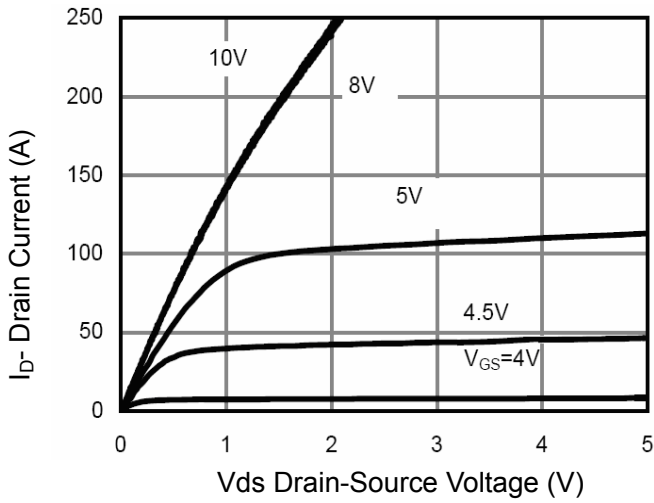


Figure 1 Output Characteristics

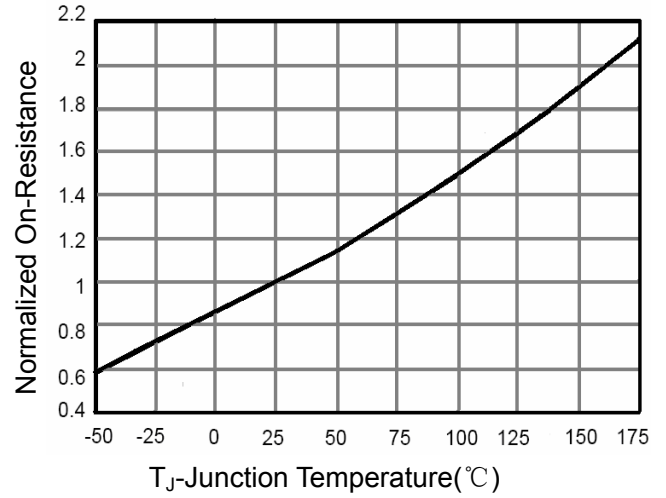


Figure 4 Rdson-Junction Temperature

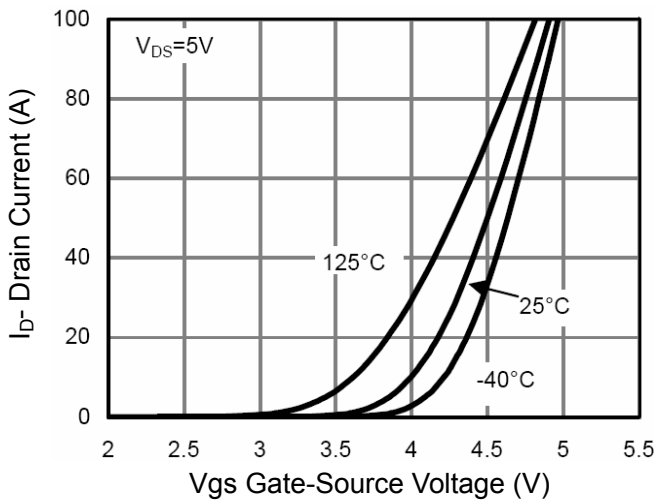


Figure 2 Transfer Characteristics

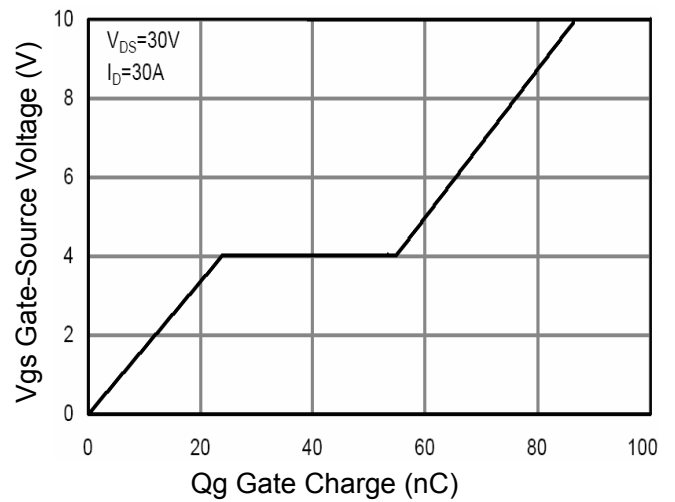


Figure 5 Gate Charge

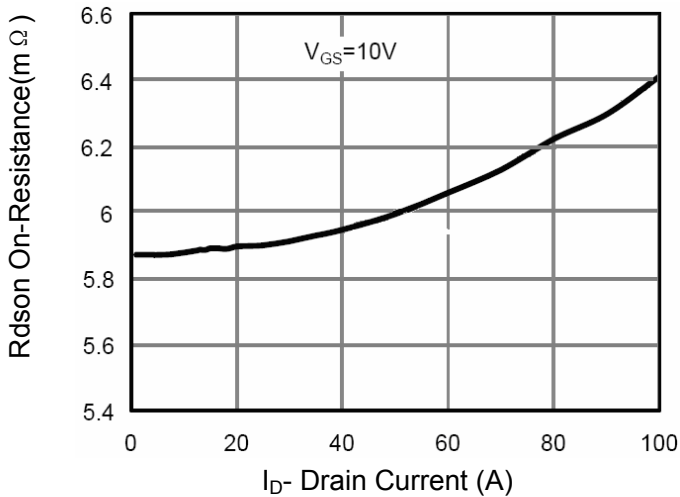


Figure 3 Rdson- Drain Current

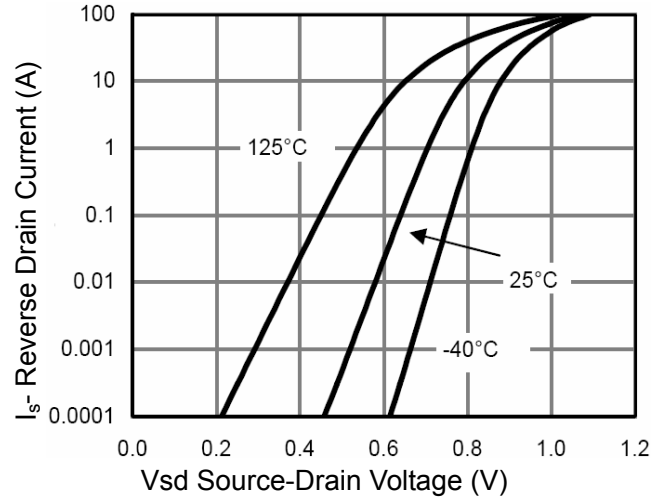


Figure 6 Source- Drain Diode Forward

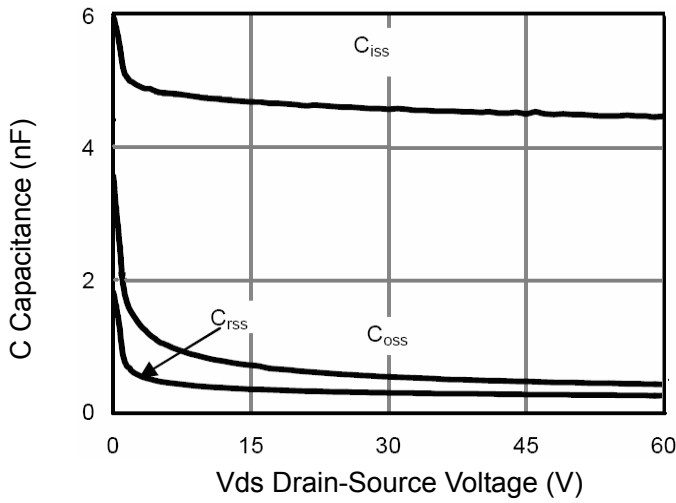


Figure 7 Capacitance vs Vds

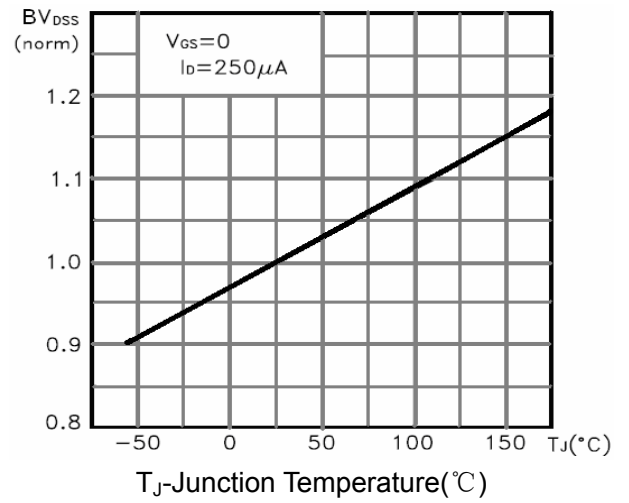


Figure 9  $BV_{DSS}$  vs Junction Temperature

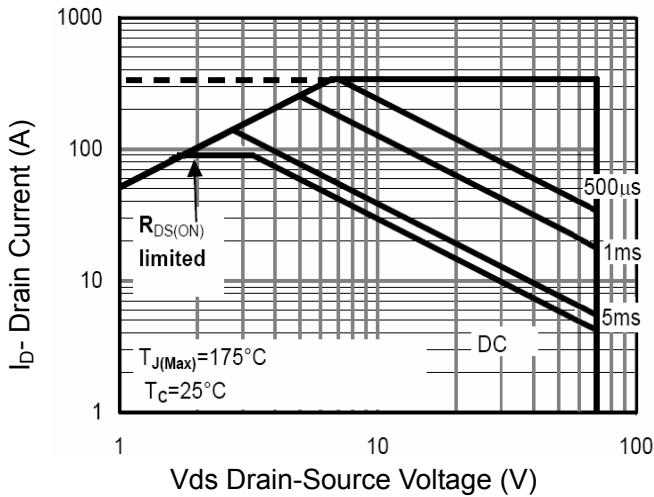


Figure 8 Safe Operation Area

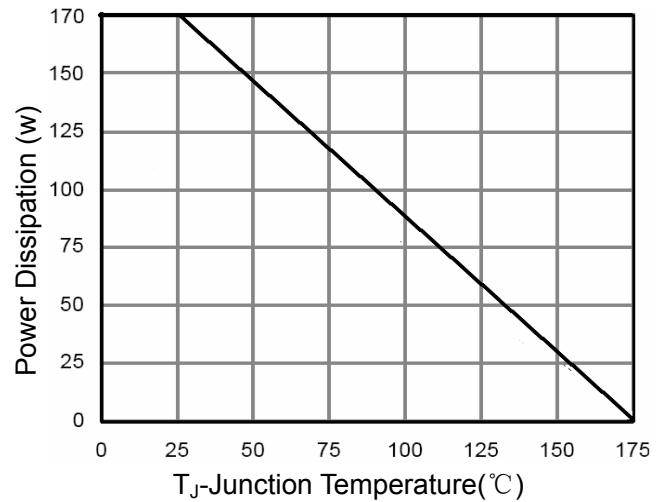


Figure 10 Power De-rating

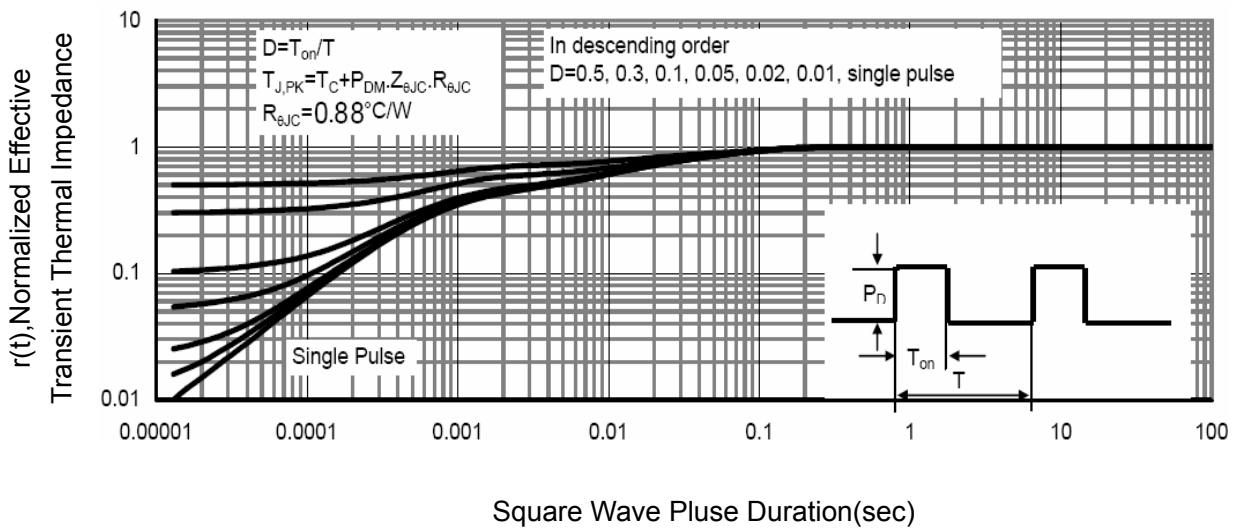
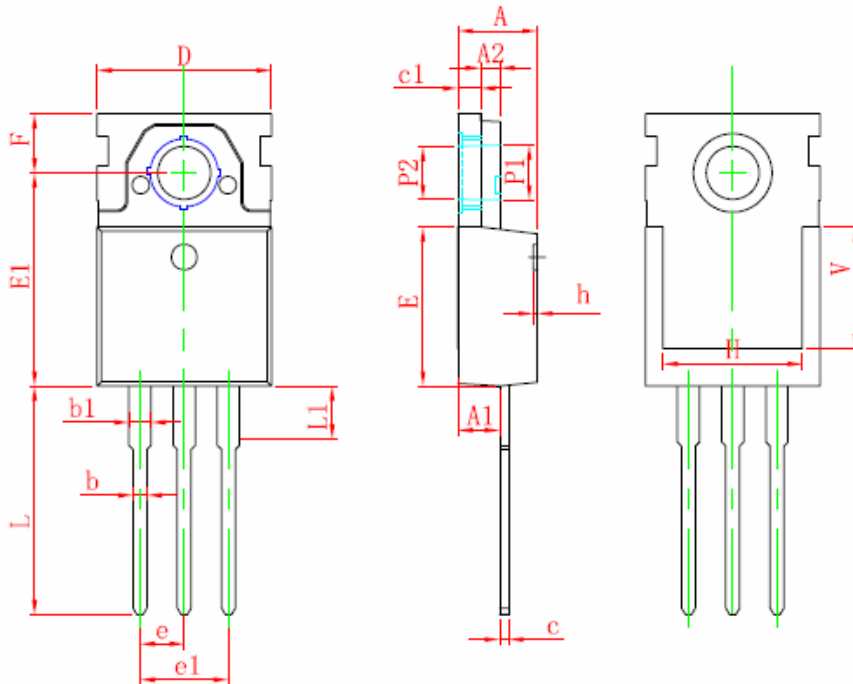


Figure 11 Normalized Maximum Transient Thermal Impedance

**TO-220H-3L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
A2	1.000	1.200	0.039	0.047
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.820	10.220	0.387	0.402
E	8.950	9.350	0.352	0.368
E1	12.000	12.500	0.472	0.492
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	3.250	3.550	0.128	0.140
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.930	13.330	0.509	0.525
L1	3.450	3.850	0.136	0.152
P1	3.15 TYP.		0.124 TYP.	
P2	3.05 TYP.		0.120 TYP.	
V	6.900 REF.		0.272 REF.	

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